

Magneto-optical studies of quantum states of two-dimensional hole gas at single Ga_{1-x}Al_xAs/GaAs heterojunction

L. Bryja

Acta Physica Polonica **106**, 131 (2004)

Magnetic-field-induced excitons in photoluminescence from heavily doped p-type Ga_{1-x}Al_xAs/GaAs single heterojunction

L. Bryja, M. Kubisa, K. Ryczko, J. Misiewicz, R. Stępniewski, M. Byszewski, M. Potemski, D. Reuter, A. Wieck

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X-ray, optical and electrical characterization of doped nanocrystalline titanium oxide thin films

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Photoreflectance and photoluminescence study of step-like GaInNAs/GaInNAs/GaAs quantum wells

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Post-growth annealing of GaInNAs layers and GaInNAs/GaAs multiple quantum wells studied by photoreflectance spectroscopy

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The energy-fine structure of GaInNAs/GaAs multiple quantum wells grown at different temperatures and postgrown annealed

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